

V-Ni-based nitride heterostructure as a highly efficient electrode for flexible all-solid-state supercapacitors

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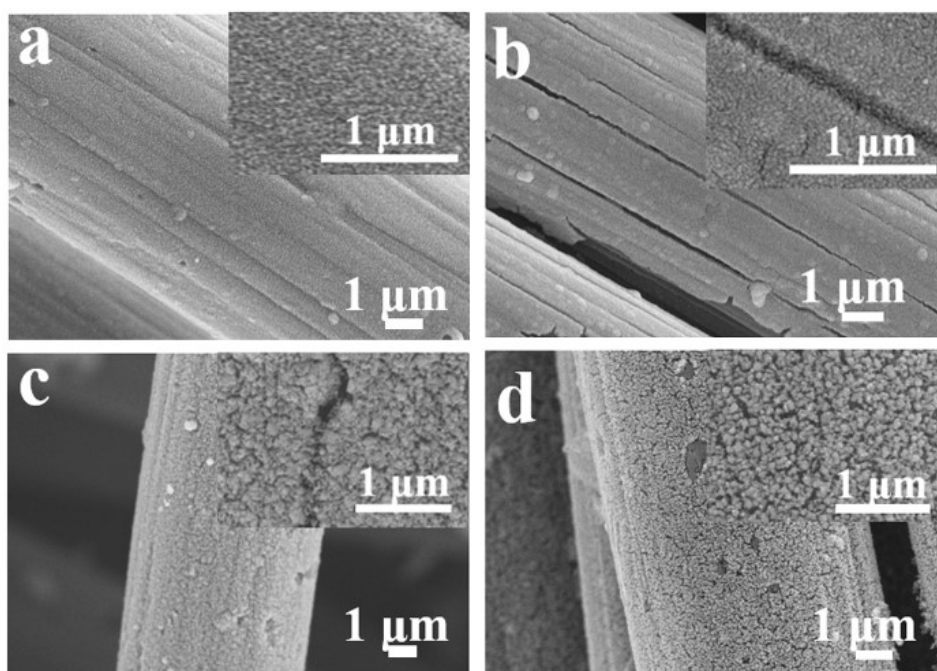


Figure S1. SEM images of VN/Ni₃N-Ni/CC at different nitriding temperature of (a) 400 °C, (b) 500 °C, (c) 600 °C and (d) 700 °C.

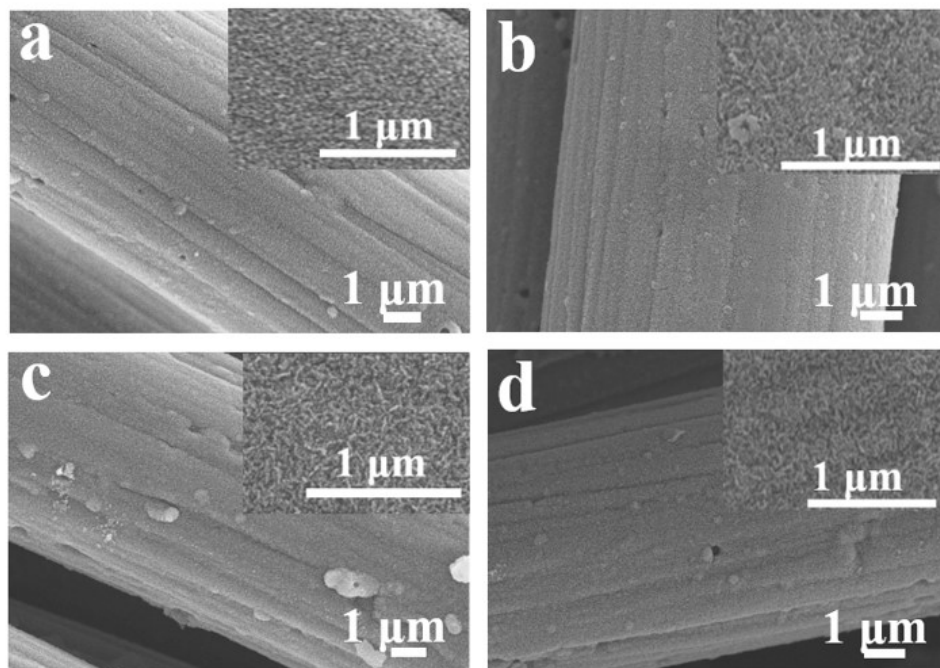


Figure S2. SEM images of VN/Ni₃N-Ni/CC for different nitriding time of (a) 2 h, (b) 3 h, (c) 4 h and (d) 5 h at 400°C.

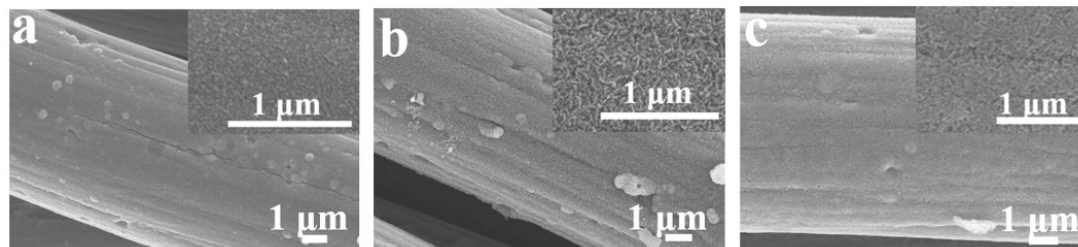


Figure S3. SEM images of VN/Ni₃N-Ni/CC at different metal molar atomic ratios of (a) Ni:V=1:2, (b) Ni:V=1:1, (c) Ni:V=2:1.

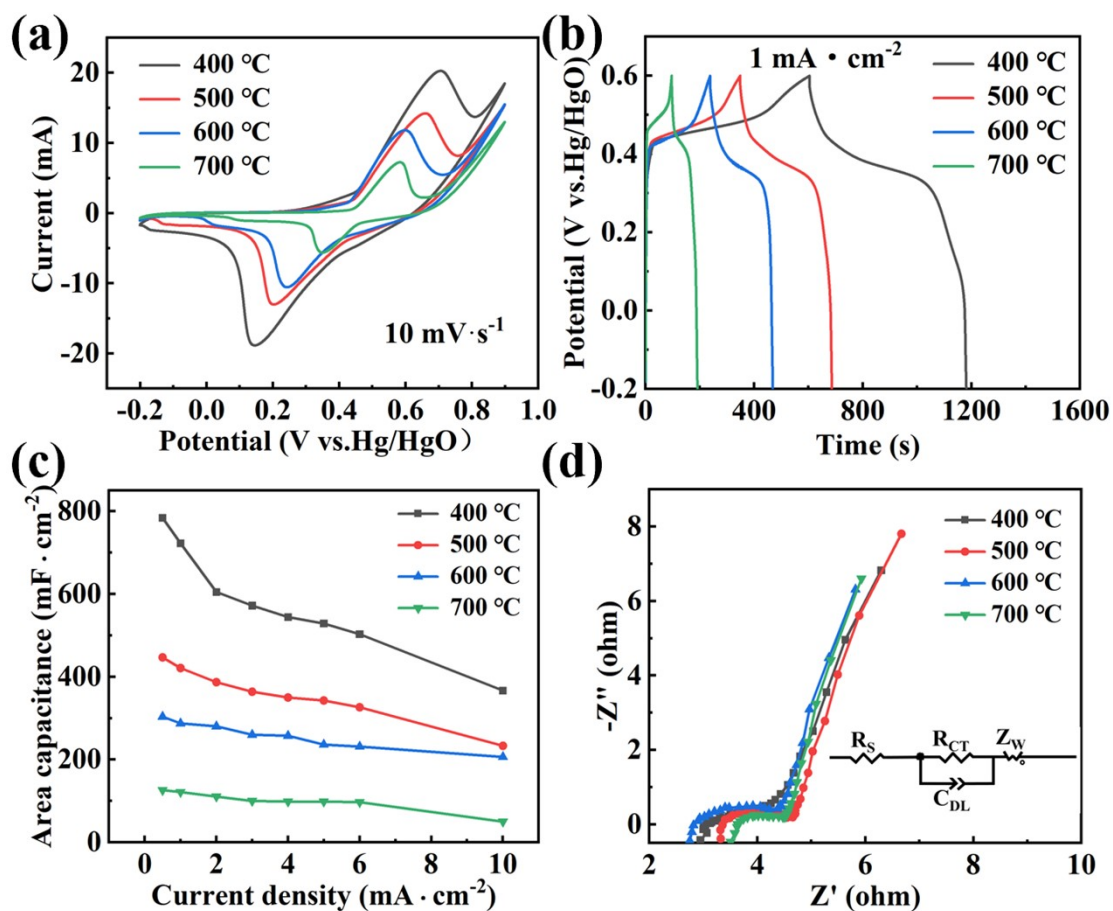


Figure S4. The comparison of electrochemical performances of the obtained VN/Ni₃N-Ni/CC at different nitriding temperatures: (a) CV, (b) GCD, (c) area capacitance and (d) EIS curves.

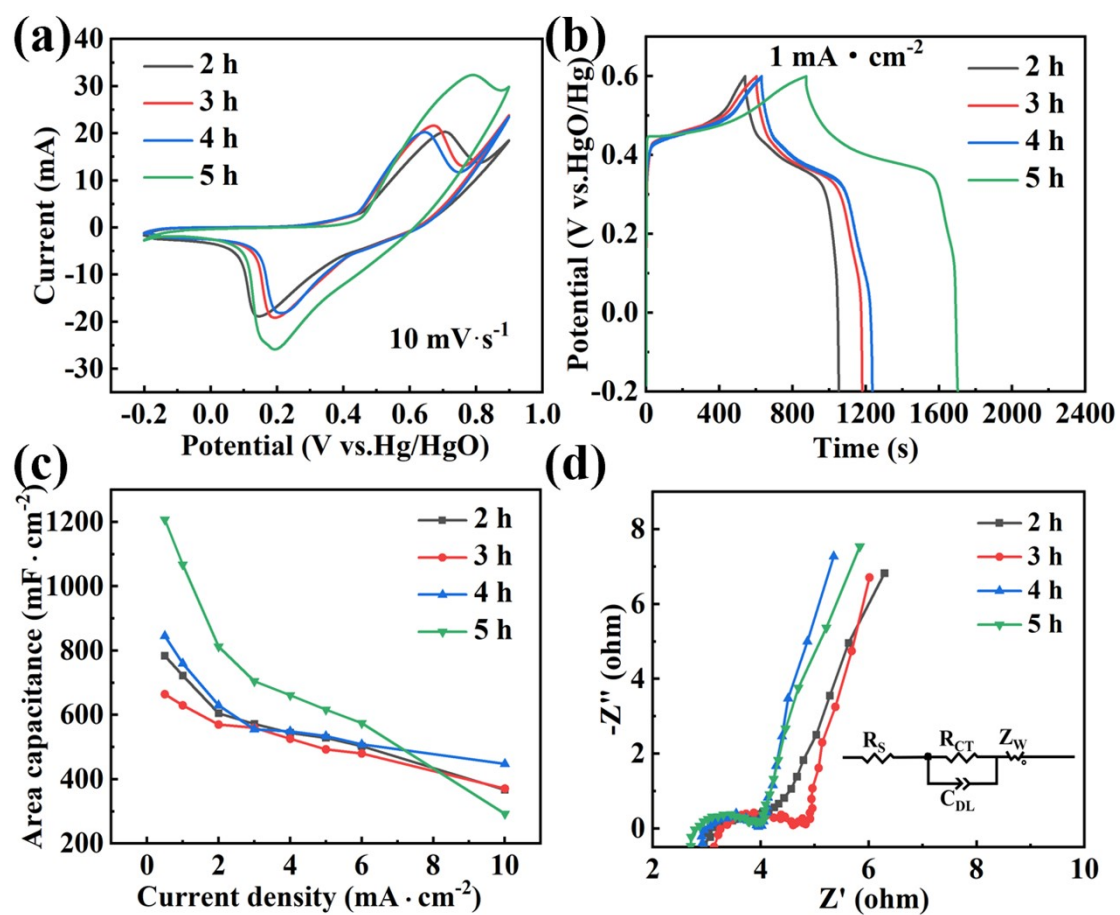


Figure S5. The comparison of electrochemical performances of the obtained VN/Ni₃N-Ni/CC at different nitriding time: (a) CV, (b) GCD, (c) area capacitance and (d) EIS curves.

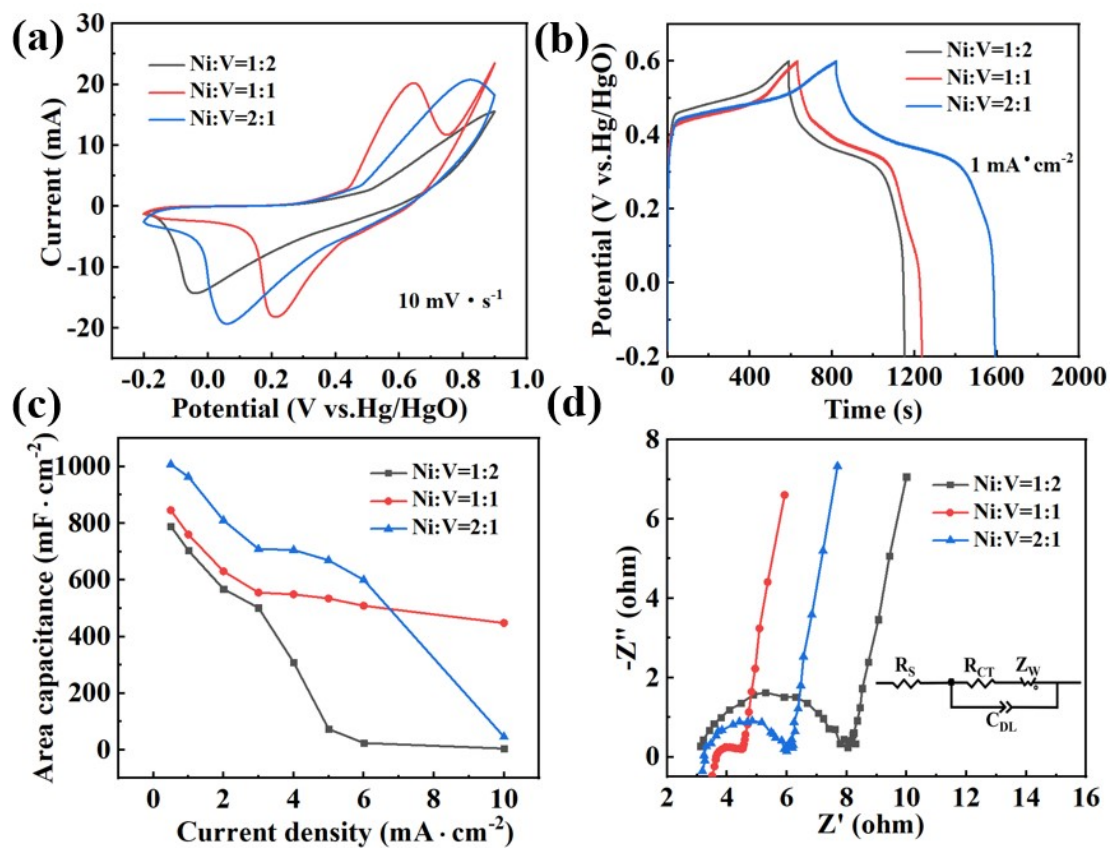


Figure S6. The comparison of electrochemical performances of the obtained VN/Ni₃N-Ni/CC at different atomic ratios of Ni:V=1:2, Ni:V=1:1, Ni:V=2:1: (a) CV, (b) GCD, (c) area capacitance and (d) EIS curves.